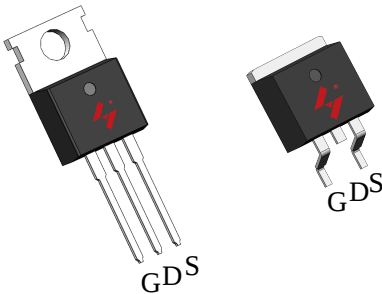


N-Channel Enhancement Mode MOSFET

Feature Description

- 30V/140A
 $R_{DS(ON)}=2.2m\Omega(typ.)@V_{GS} = 10V$
 $R_{DS(ON)}=2.7m\Omega(typ.) @V_{GS}= 4.5V$
- 100% avalanche tested
- Excellent CdV/dt effect decline
- Lead- Free Device Available

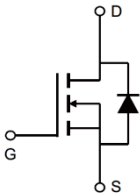
Pin Description



TO-220FB-3L TO-263-2L

Applications

- Switching Application
- Power Management for DC/DC



N-Channel MOSFET

Ordering and Marking Information

 P HY3403 YYXXXJWW G	 B HY3403 YYXXXJWW G	Package Code P: TO-220FB-3L B: TO-263-2L	Date Code YYXXX WW	Assembly Material G:lead Free
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Note: HUAYI lead-free products contain molding compounds/die attach materials and 100% matte tin plate Termination finish;which are fully compliant with RoHS. HUAYI lead-free products meet or exceed the lead-Free requirements of IPC/JEDEC J-STD-020 for MSL classification at lead-free peak reflow temperature. HUAYI defines “Green” to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUAYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this product and/or to this document at any time without notice.

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Drain Current-Continuous	Tc=25°C	140	A
Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	Tc=25°C	560	A
I _D	Continuous Drain Current	Tc=25°C	140	A
		Tc=100°C	101	A
P _D	Maximum Power Dissipation	Tc=25°C	115	W
		Tc=100°C	57.5	W
R _{θJC}	Thermal Resistance, Junction-to-Case		1.3	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient **		62.5	°C/W
E _{AS}	Single Pulsed-Avalanche Energy ***	L=0.3mH	186	mJ

Note: * Repetitive rating ; pulse width limited by max junction temperature.
 ** Surface mounted on FR-4 board.
 *** Limited by T_{Jmax} , starting T_J=25°C, L = 0.3mH, R_G= 25Ω, V_{GS}=10V.

Electrical Characteristics (Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HY3403			Unit
			Min	Typ	Max	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250uA	30	-	-	V
I _{DSS}	Drain-to-Source LeakageCurrent	V _{DS} =30V, V _{GS} =0V	-	-	1	uA
			T _J =55°C	-	-	5
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250uA	1	1.5	3	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)*}	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =70A	-	2.2	2.8	mΩ
		V _{GS} =4.5V, I _{DS} =70A	-	2.7	3.4	mΩ
Diode Characteristics						
V _{SD} *	Diode Forward Voltage	I _{SD} =70A, V _{GS} =0V	-	0.8	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =70A, dI _{SD} /dt=100A/us	-	23	-	ns
Q _{rr}	Reverse Recovery Charge		-	58	-	nC

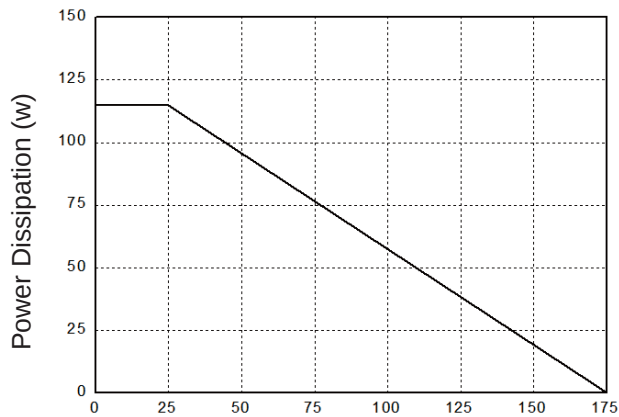
Electrical Characteristics (Cont.) (T_c =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HY3403			Unit
			Min	Typ	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1.9	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V,	-	4726	-	pF
C _{oss}	Output Capacitance	V _{DS} =25V,	-	469	-	
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	-	322	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V,R _G =4Ω, I _{DS} =70A,V _{GS} =10V	-	13	-	ns
T _r	Turn-on Rise Time		-	11	-	
t _{d(OFF)}	Turn-off Delay Time		-	41	-	
T _f	Turn-off Fall Time		-	14	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =24V, V _{GS} =10V, I _D =70A,	-	120	-	nC
Q _{gs}	Gate-Source Charge		-	9	-	
Q _{gd}	Gate-Drain Charge		-	26	-	

Note: *Pulse test; pulse width ≤ 300us, duty cycle ≤ 2%

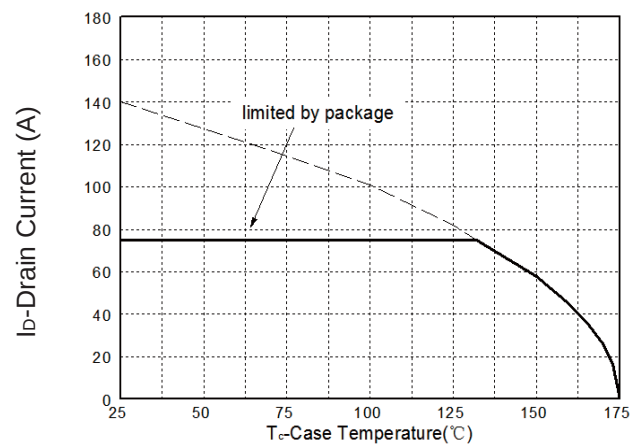
Typical Operating Characteristics

Power Dissipation



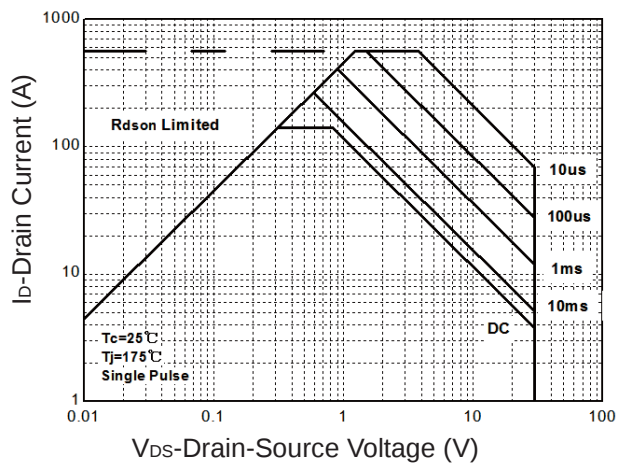
Tc-Case Temperature (°C)

Drain Current



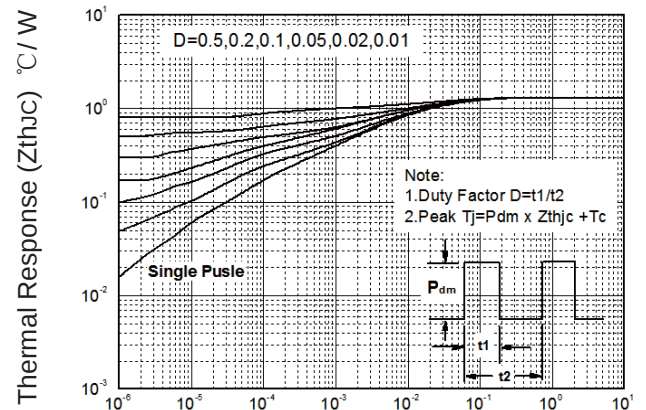
Tc-Case Temperature (°C)

Safe Operation Area



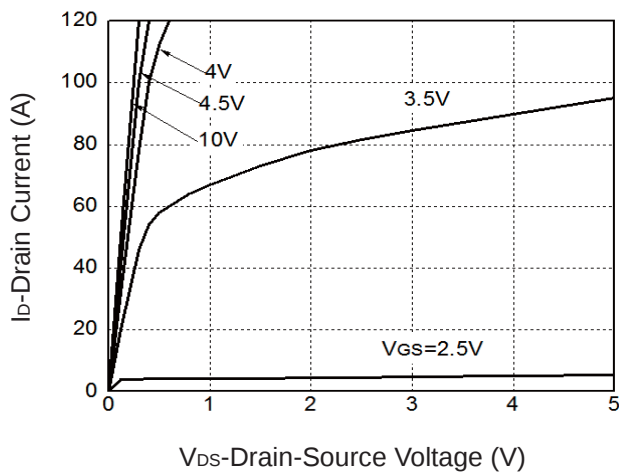
VDS-Drain-Source Voltage (V)

Thermal Transient Impedance



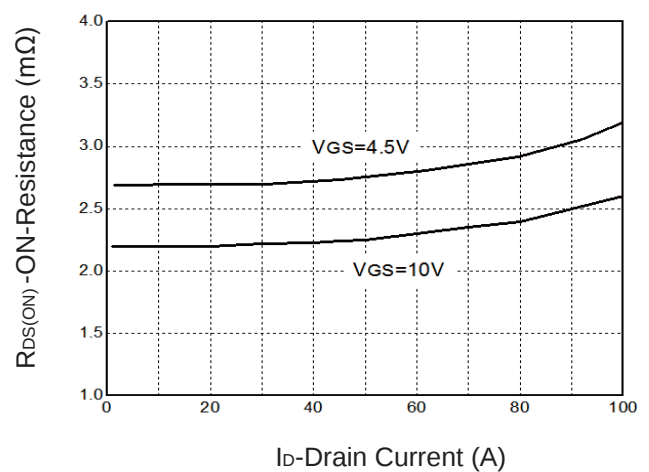
Maximum Effective Transient Thermal Impedance, Junction-to-Case

Output Characteristics



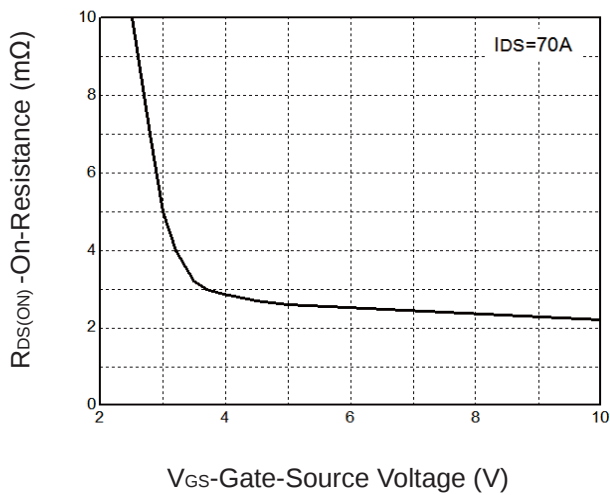
VDS-Drain-Source Voltage (V)

Drain-Source On Resistance

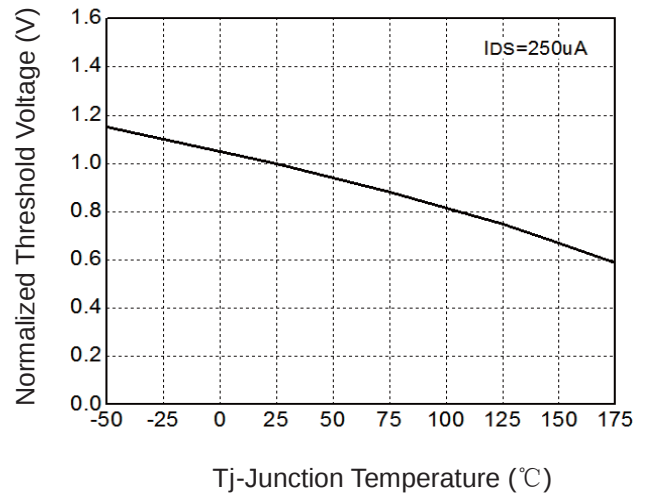


Typical Operating Characteristics(Cont.)

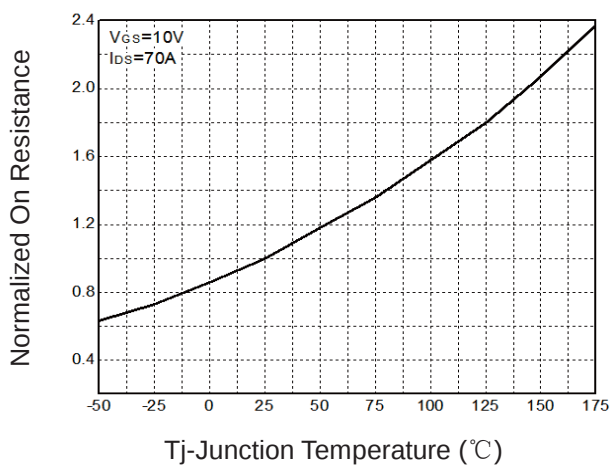
Gate-Source On Resistance



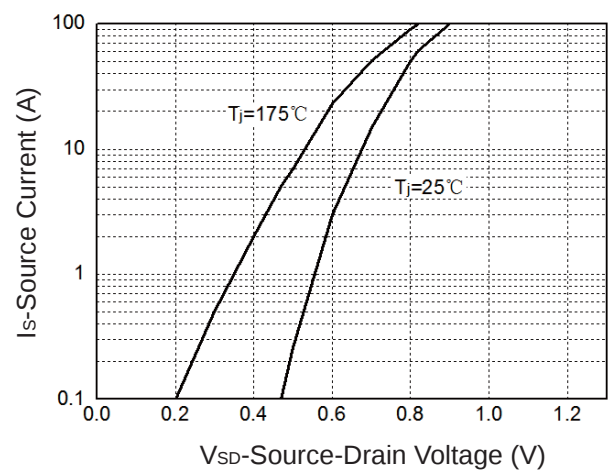
Gate Threshold Voltage



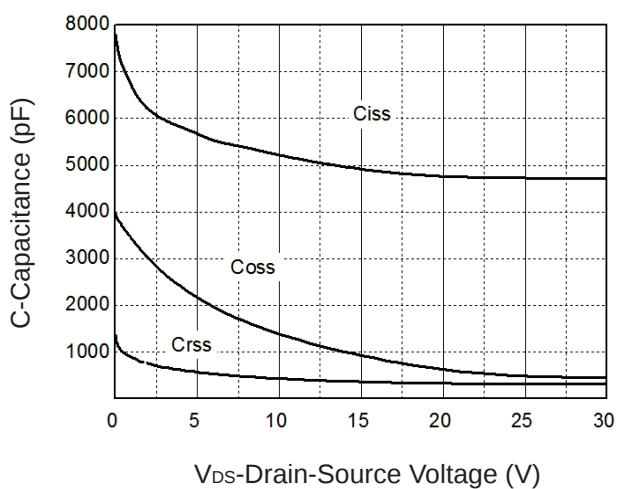
On-Resistance vs. Temperature



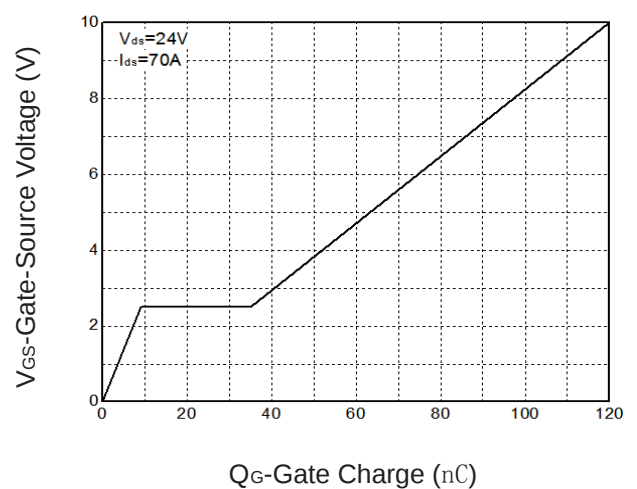
Source- Drain Diode Forward



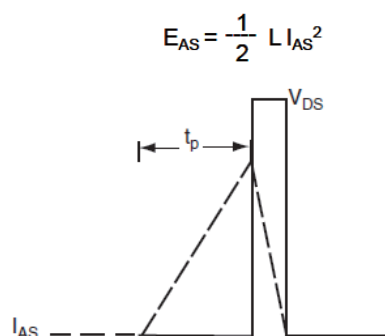
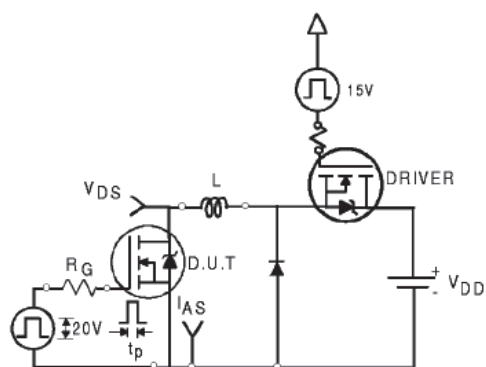
Capacitance Characteristics



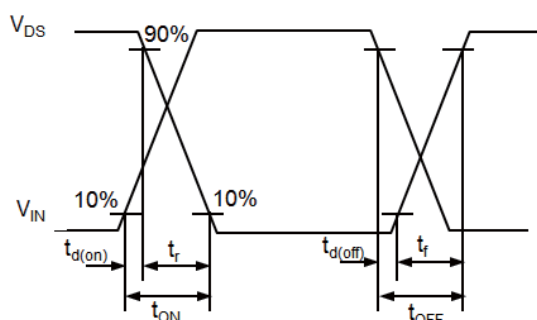
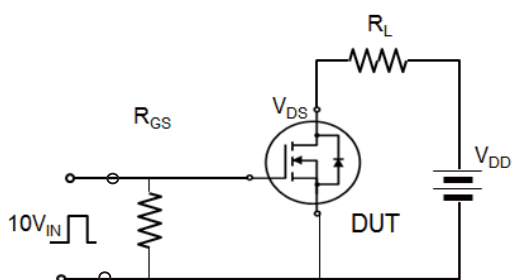
Gate Charge Characteristics



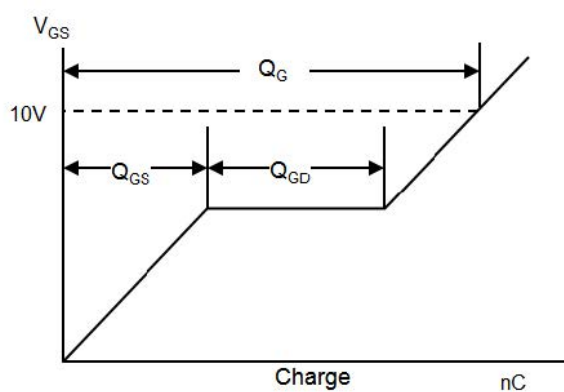
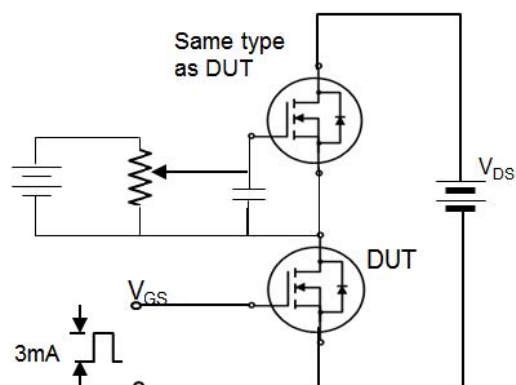
Avalanche Test Circuit



Switching Time Test Circuit

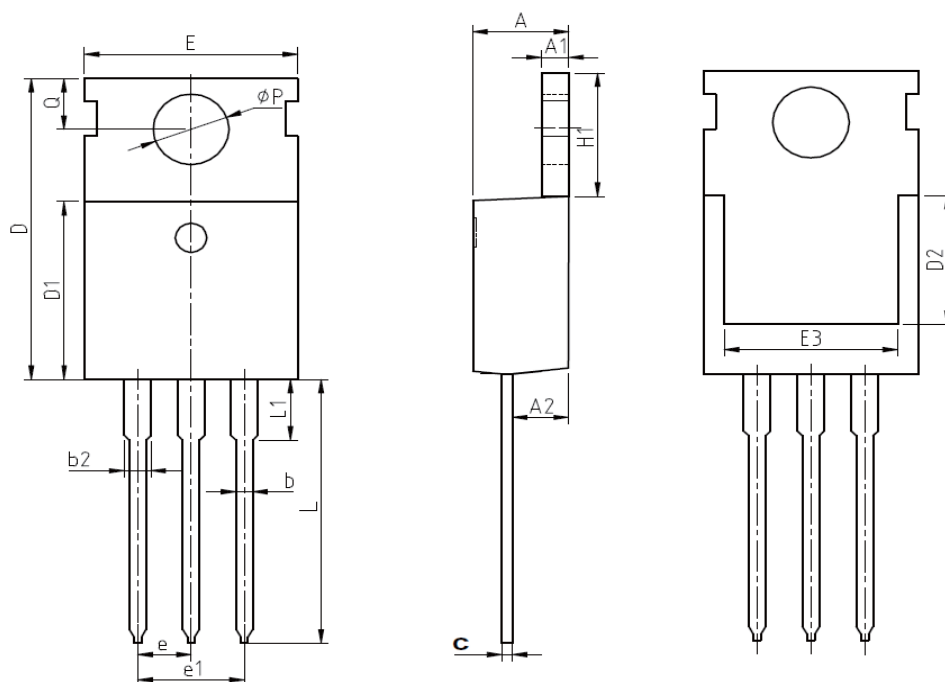


Gate Charge Test Circuit



Package Information

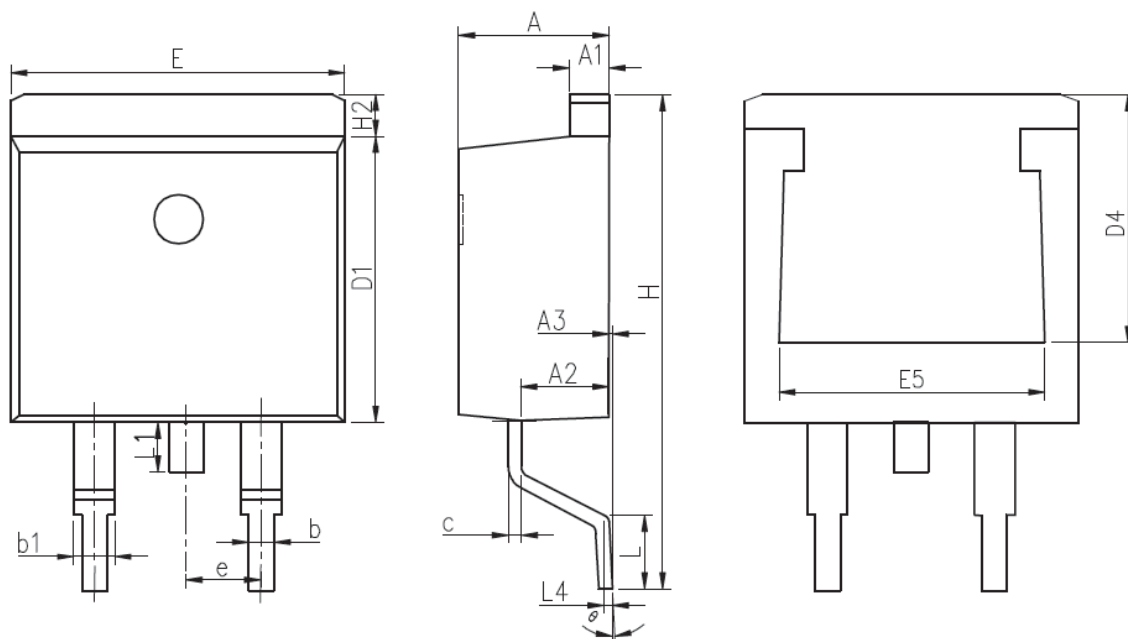
TO-220FB-3L



COMMON DIMENSIONS

SYMBOL	mm		
	MIN		MAX
A	4.37	4.57	4.77
A1	1.25	1.30	1.45
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.40	0.50	0.65
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ΦP	3.40	3.60	3.80
Q	2.60	2.80	3.00

TO-263-2L



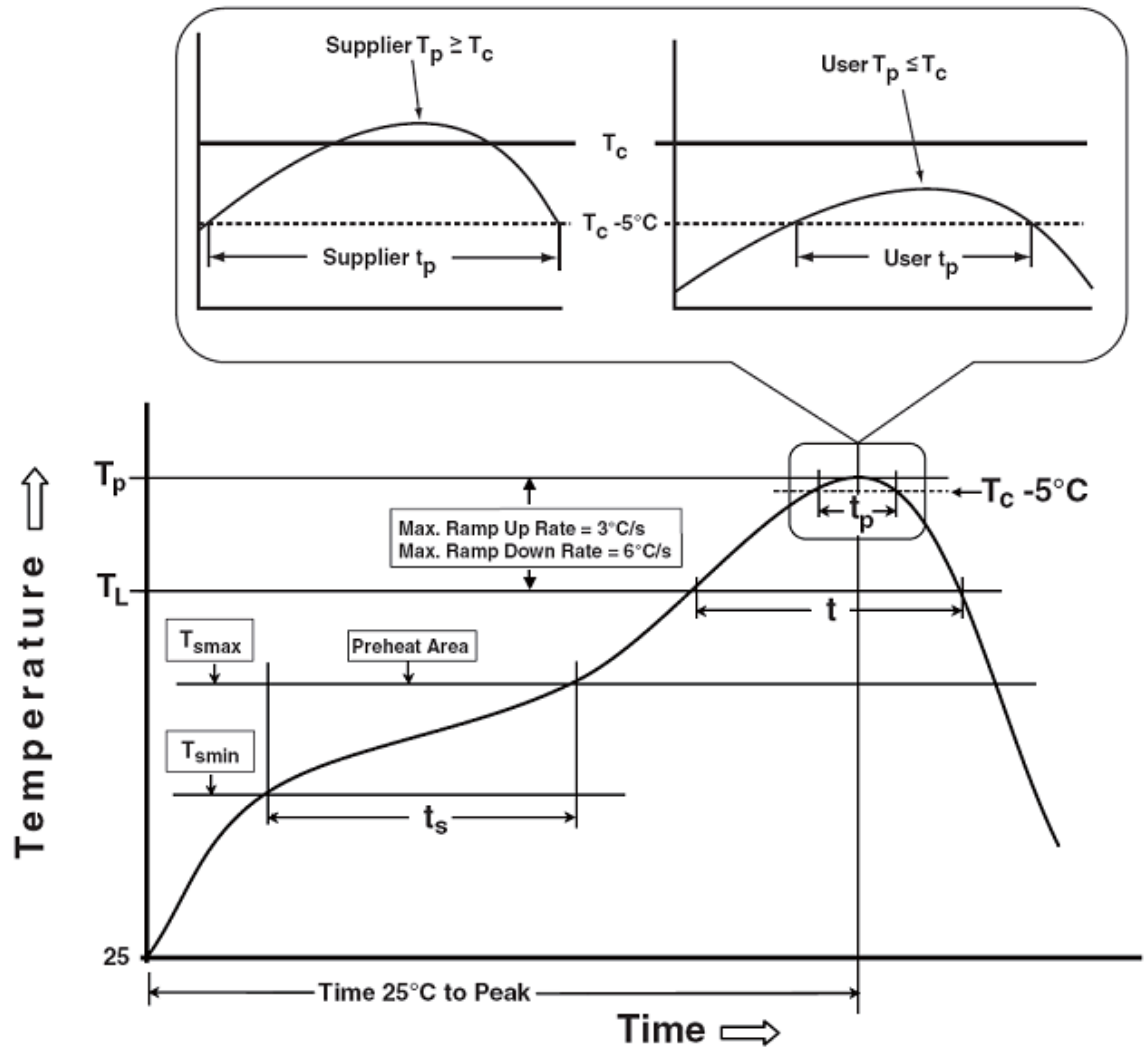
COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
A3	0	0.13	0.25
b	0.7	0.81	0.96
b1	1.17	1.27	1.47
c	0.3	0.38	0.53
D1	8.5	8.7	8.9
D4	6.6	-	-
E	9.86	10.16	10.36
E5	7.06	-	-
e	2.54 BSC		
H	14.7	15.1	15.5
H2	1.07	1.27	1.47
L	2	2.3	2.6
L1	1.4	1.55	1.7
L4	0.25 BSC		
θ	0°	5°	9°

Device Per Unit

Package Type	Unit	Quantity
TO-220FB-3L	Tube	50
TO-263-2L	Tube	50

Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ ≥2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	168 Hrs /500 Hrs /1000 Hrs, Bias @ 150°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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